

FDMC4435BZ

P-Channel Power Trench® MOSFET

-30V, -18A, 20.0mΩ

Features

- Max $r_{DS(on)}$ = 20.0mΩ at $V_{GS} = -10V$, $I_D = -8.5A$
- Max $r_{DS(on)}$ = 37.0mΩ at $V_{GS} = -4.5V$, $I_D = -6.3A$
- Extended V_{GSS} range (-25V) for battery applications
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability
- HBM ESD protection level >7kV typical (Note 4)
- 100% UIL Tested
- Termination is Lead-free and RoHS Compliant

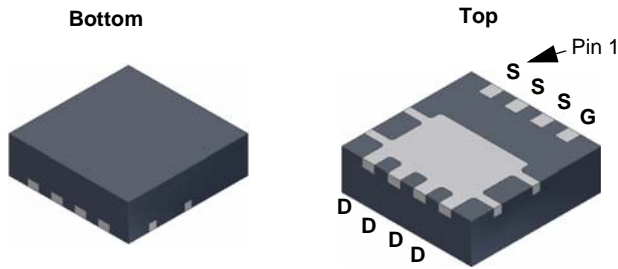


General Description

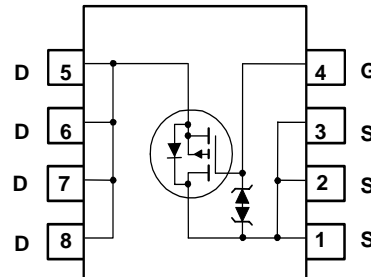
This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Applications

- High side in DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook



Power 33



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	-30	V
V_{GS}	Gate to Source Voltage	±25	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	-18	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	-31	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	-8.5	
	-Pulsed	-50	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	24	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	31	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC4435BZ	FDMC4435BZ	Power 33	13"	12mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		22		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$			-1 -100	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 25\text{V}$, $V_{DS} = 0\text{V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\mu\text{A}$	-1.0	-1.9	-3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$, referenced to 25°C		-5.3		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -10\text{V}$, $I_D = -8.5\text{A}$		14.6	20.0	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}$, $I_D = -6.3\text{A}$		23.1	37.0	
		$V_{GS} = -10\text{V}$, $I_D = -8.5\text{A}$, $T_J = 125^\circ\text{C}$		20.7	28.0	
g_{FS}	Forward Transconductance	$V_{DD} = -5\text{V}$, $I_D = -8.5\text{A}$		24		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -15\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1540	2045	pF
C_{oss}	Output Capacitance			295	395	pF
C_{rss}	Reverse Transfer Capacitance			260	385	pF
R_g	Gate Resistance		$f = 1\text{MHz}$		5.1	Ω

Switching Characteristics

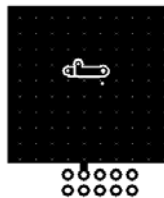
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -15\text{V}$, $I_D = -8.5\text{A}$, $V_{GS} = -10\text{V}$, $R_{GEN} = 6\Omega$		10	20	ns	
t_r	Rise Time			6	12	ns	
$t_{d(off)}$	Turn-Off Delay Time			34	55	ns	
t_f	Fall Time			20	36	ns	
Q_g	Total Gate Charge		$V_{GS} = 0\text{V}$ to -10V		33	46	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{V}$ to -4.5V	$V_{DD} = -15\text{V}$, $I_D = -8.5\text{A}$		17	24	nC
Q_{gs}	Gate to Source Charge				5		nC
Q_{gd}	Gate to Drain "Miller" Charge				9		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = -8.5\text{A}$ (Note 2)		0.92	1.5	V
		$V_{GS} = 0\text{V}$, $I_S = -1.9\text{A}$ (Note 2)		0.75	1.2	
t_{rr}	Reverse Recovery Time	$I_F = -8.5\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		22		ns
Q_{rr}	Reverse Recovery Charge			11		nC

NOTES:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $53^\circ\text{C}/\text{W}$ when mounted on a 1in^2 pad of 2 oz copper



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < $300\mu\text{s}$, Duty cycle < 2.0%.

3: Starting $T_J = 25^\circ\text{C}$, $L = 1\text{mH}$, $I_{AS} = -7\text{A}$, $V_{DD} = -27\text{V}$, $V_{GS} = -10\text{V}$.

4: The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

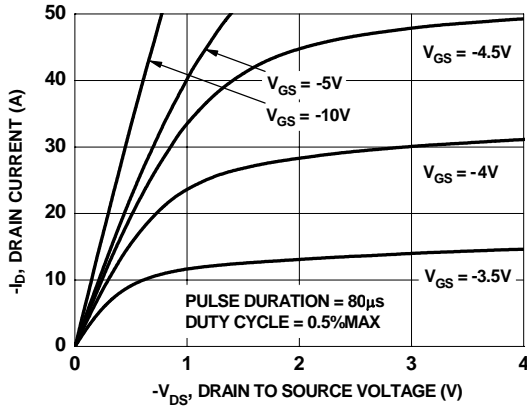


Figure 1. On-Region Characteristics

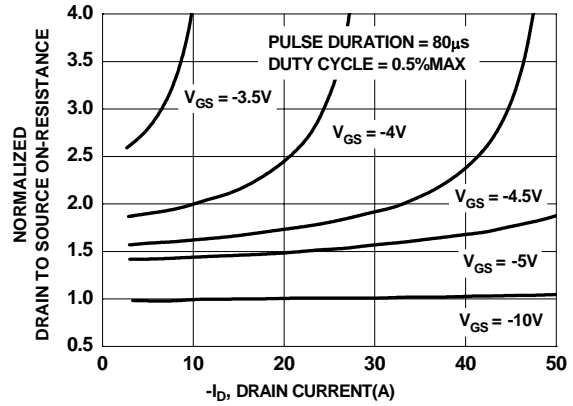


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

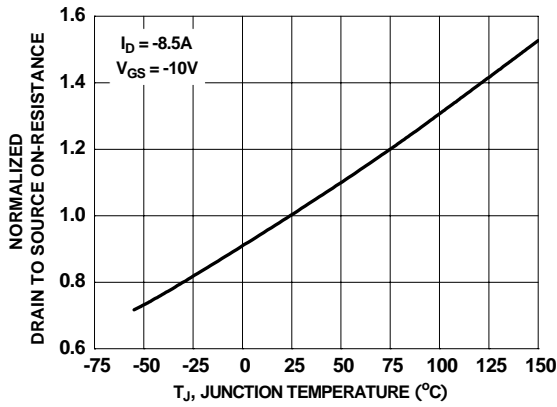


Figure 3. Normalized On-Resistance vs Junction Temperature

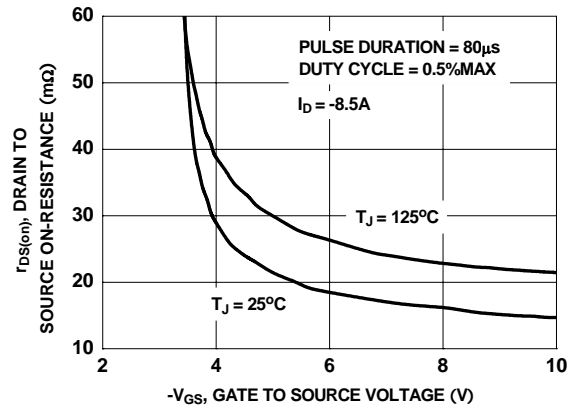


Figure 4. On-Resistance vs Gate to Source Voltage

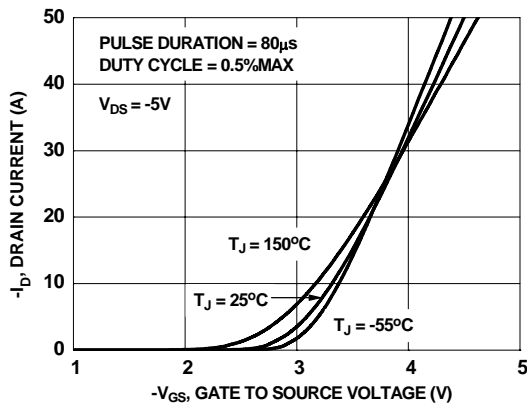


Figure 5. Transfer Characteristics

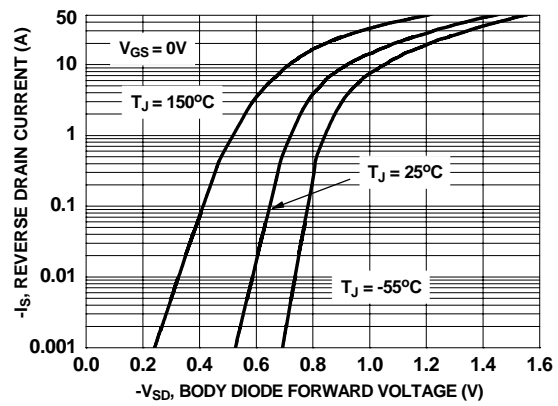


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

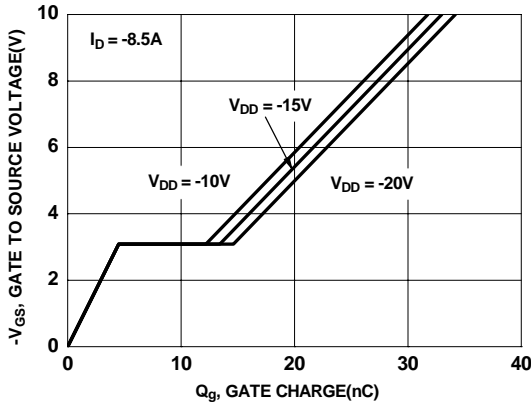


Figure 7. Gate Charge Characteristics

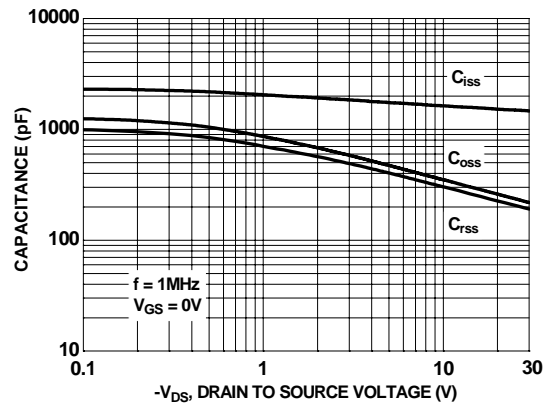


Figure 8. Capacitance vs Drain to Source Voltage

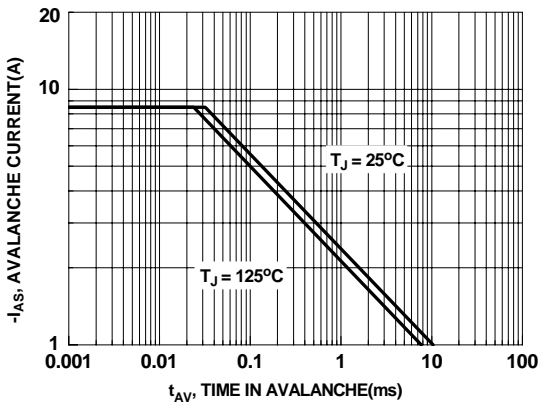


Figure 9. Unclamped Inductive Switching Capability

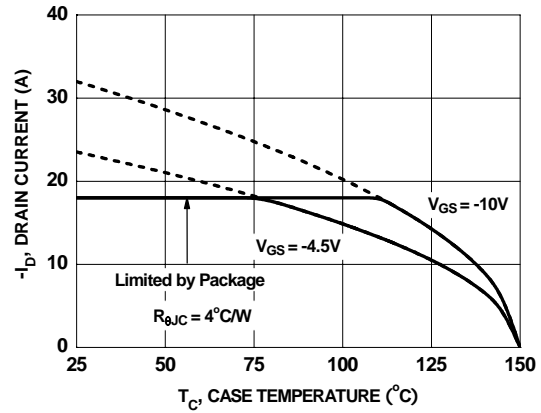


Figure 10. Maximum Continuous Drain Current vs Case Temperature

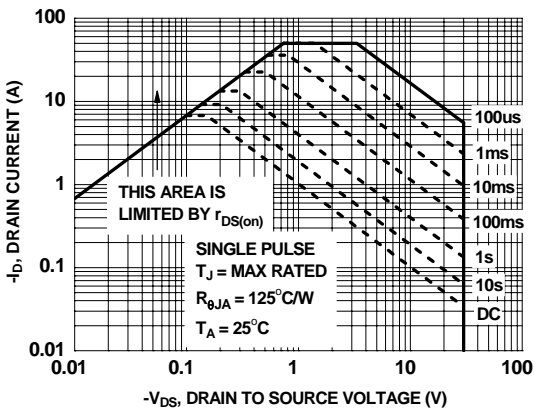


Figure 11. Forward Bias Safe Operating Area

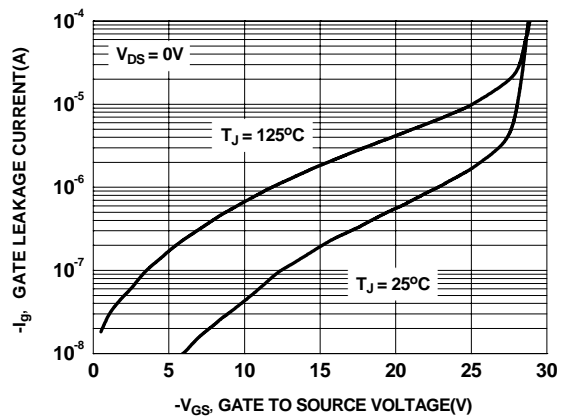


Figure 12. I_{gss} vs V_{gss}

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

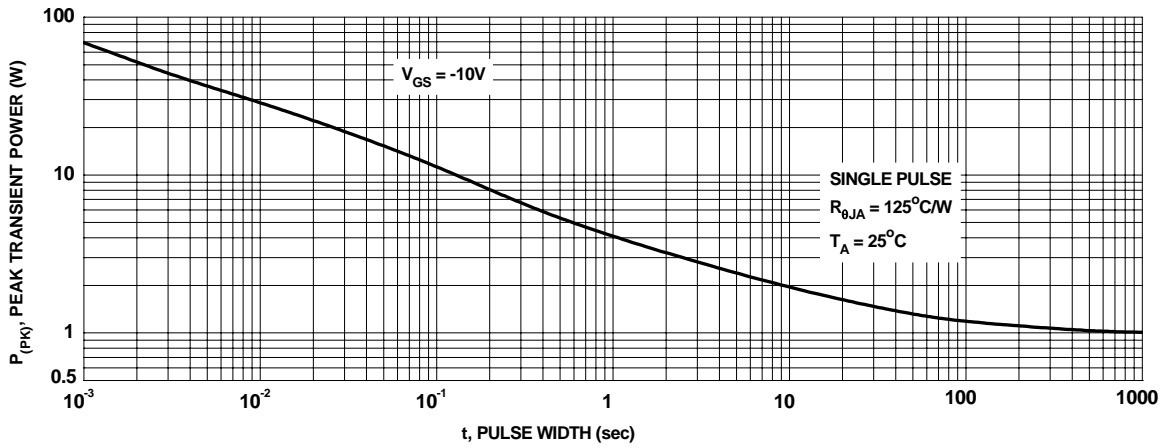


Figure 13. Single Pulse Maximum Power Dissipation

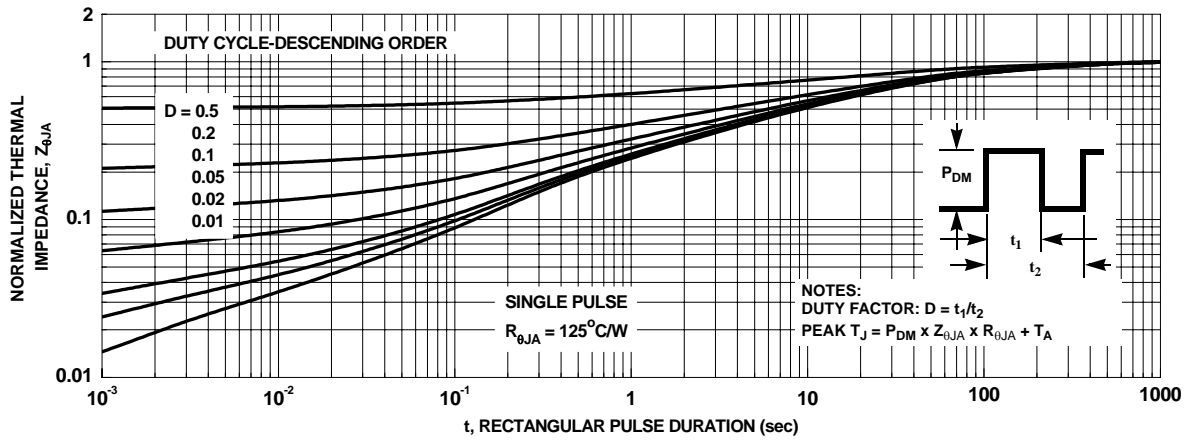




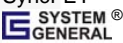


Figure 14. Transient Thermal Response Curve



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